

CDSV6-756-G

Forward Current: 0.15A
Reverse Voltage: 75V
RoHS Device

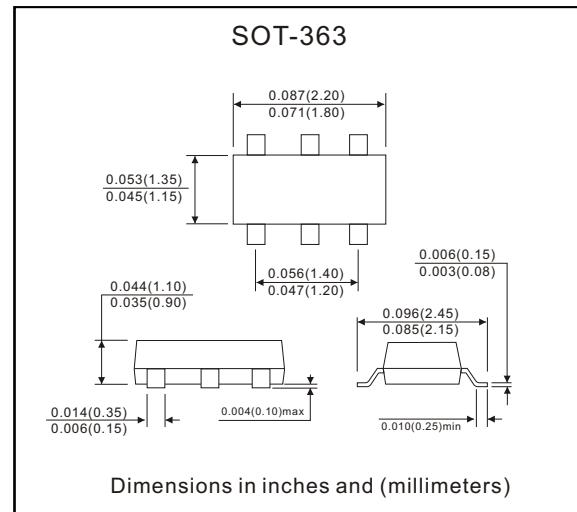
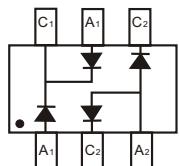


Features

- Fast switching speed.
- Ultra small surface mount package.
- For general purpose switching applications.
- High conductance.

Marking: KCA

Diagram:



Maximum Rating (at TA=25°C unless otherwise noted)

Parameter	Symbol	Limits	Unit
Peak repetitive peak reverse voltage Working peak reverse voltage DC blocking voltage	V _{RRM} V _{RWM} V _R	75	V
Forward continuous current	I _{FM}	300	mA
Averaged rectified output current	I _O	150	mA
Non-repetitive peak forward surge current @t=1.0μS @t=1.0S	I _{FSM}	2.0 1.0	A
Power dissipation	P _D	200	mW
Thermal resistance, junction to ambient air	R _{θJA}	625	°C/W
Operation junction temperature	T _J	150	°C
Storage temperature range	T _{STG}	-65 ~ +150	°C

Electrical Characteristics (at TA=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Reverse breakdown voltage	I _R =2.5μA	V _{(BR)R}	75			V
Forward voltage	I _F =1mA I _F =10mA I _F =50mA I _F =150mA	V _F			0.715 0.855 1.000 1.250	V
Reverse leakage current	V _R =75V V _R =20V	I _R			2.5 0.025	μA
Junction capacitance	V _R =0V, f=1.0MHz	C _T			2	pF
Reverse recovery time	I _F =I _R =10mA, I _{rr} =0.1×I _R , R _L =100Ω	t _{rr}			4	nS

SMD Switching Diode Arrays

COMCHIP
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ELECTRICAL CHARACTERISTIC CURVES (CDSV6-756-G)

Fig.1 Forward Characteristics

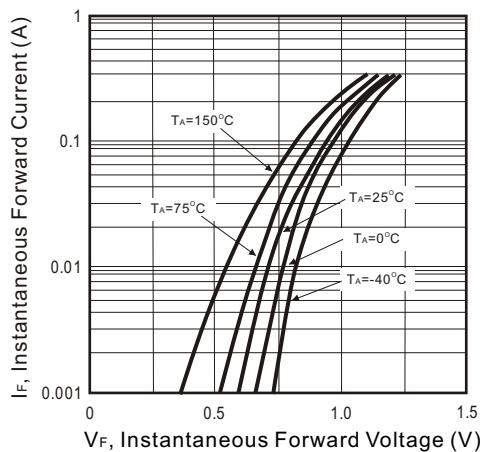


Fig.2 Reverse Characteristics

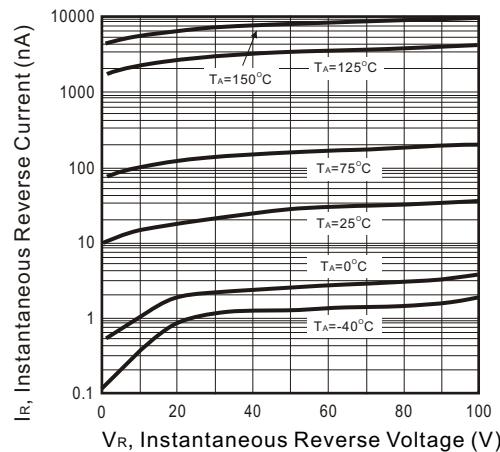


Fig.3 Capacitance Between Terminals Characteristics

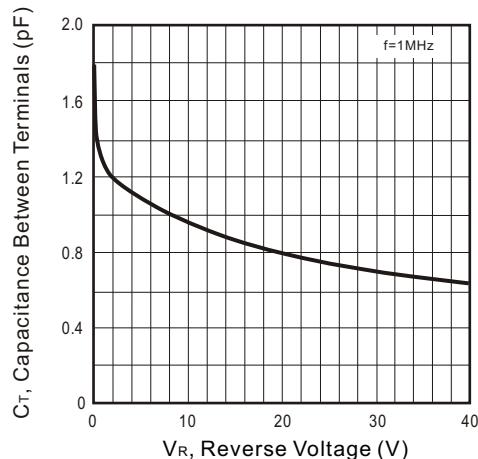


Fig.4 Power Derating Curve

